

8. Method according to Claims 5 and 7, characterized in that the gases SF₆, HBr, or He/O₂ are used for the dry etching process.

9. Method according to one of Claims 1-8, characterized in that a liner is deposited onto the surfaces in contact with the contact material (16) before the contact material (16) is introduced.

10. Method according to Claim 9, characterized in that the liner is composed of Ti or Ti/TiN.

11. Method according to one of Claims 1-10, characterized in that tungsten is used as the contact material (16).

12. Method according to one of Claims 1-11, characterized in that the contact material (16) and the resin mask (3) are removed via a CMP process (chemical-mechanical polishing process).

13. Method according to one of Claims 1-12, characterized in that a second contact hole (5) up to a second contact surface to be contacted is formed together with the first contact hole (4) in the same way.

14. Method according to Claim 13, characterized in that a second conductor, which is insulated from the first conductor and which is connected to the contact material (16) in the second contact hole (16), is created in the insulating layer (2).

15. Method according to Claim 13, characterized in that the contact material (16) of the second contact hole (5) is connected to a second conductor in a different conduction plane.

16. Method according to one of Claims 1-15, characterized in that a layer stack is deposited onto the surface of the substrate (1), where this layer stack is composed of at least a gate oxide (9) and a cover (10), and a third contact hole (6) to the gate oxide (9) is formed, such that the first (4), or the first (4) and the second, contact hole (5) is selectively etched up to the cover (10) and after the formation is filled and covered with an auxiliary material (11), then the cover (10) is etched up to the gate oxide (9), the auxiliary material (11) is removed and then the third contact hole (6) undergoes the same method as the first (4) or the first (4) and the second contact hole (5), starting with the filling and coating with ARC material (12).

17. Method according to Claim 16, characterized in that a third conductor, which is insulated from the first conductor or from the first and the second conductor and which is connected to the contact material (16) in the third contact hole (6), is formed in the insulating layer (2).

18. Method according to Claim 16, characterized in that the contact material (16) of the third contact hole (6) is connected to a third conductor in a different conduction plane.

19. Method according to one of Claims 16-18, characterized in that the auxiliary material (11) is composed of photoresist.

20. Method according to Claim 19, characterized in that an ARC layer is deposited under the photoresist.